



《风光欣》技术资料

2SA1576

PNP TRANSISTOR

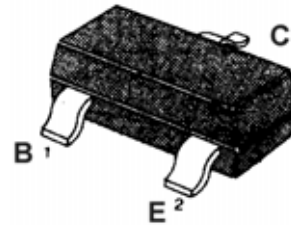
Features

Excellent h_{FE} linearity

ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CB0}	-60	V
Collector-Emitter Voltage	V_{CE0}	-50	V
Emitter -Base Voltage	V_{EB0}	-6	V
Collector Current	I_c	-0.15	A
Collector Dissipation	P_c	200	mW
Junction Temperature	T_J	150	
Storage Temperature	T_{STG}	-55 ~ +150	

SOT-323



●Electrical characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CB0}	-60	-	-	V	$I_c=-50\mu\text{A}$
Collector-emitter breakdown voltage	BV_{CE0}	-50	-	-	V	$I_c=-1\mu\text{A}$
Emitter-base breakdown voltage	BV_{EB0}	-6	-	-	V	$I_E=-50\mu\text{A}$
Collector cutoff current	I_{c0}	-	-	-0.1	μA	$V_{CE}=-60\text{V}$
Emitter cutoff current	I_{E0}	-	-	-0.1	μA	$V_{EB}=-6\text{V}$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-	-0.5	V	$I_c/I_E=-50\text{mA}/-5\text{mA}$
DC current transfer ratio	h_{FE}	120	-	560	-	$V_{CE}=-6\text{V}$, $I_c=-1\text{mA}$
Transition frequency	f_T	-	140	-	MHz	$V_{CE}=-12\text{V}$, $I_E=2\text{mA}$, $f=30\text{MHz}$
Output capacitance	C_{ob}	-	4.0	5.0	pF	$V_{CE}=-12\text{V}$, $I_E=0\text{A}$, $f=1\text{MHz}$

h_{FE} values are classified as follows:

Item	Q	R	S
h_{FE}	120~270	180~390	270~560